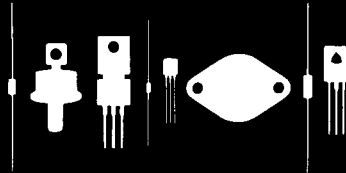


Central
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 145 Adams Avenue
 Hauppauge, New York 11788



2N3820
 P-CHANNEL JUNCTION FET
 JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3820 type is a Silicon P-Channel Junction Field Effect Transistor designed for low level amplifier applications.

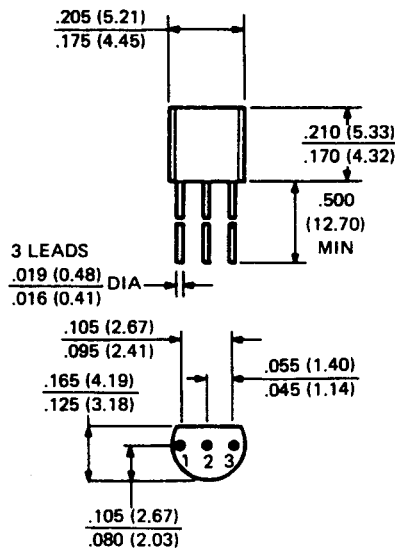
MAXIMUM RATINGS (T_A=25°C)

| | SYMBOL | | UNIT |
|---|-----------------------------------|-------------|------|
| Gate-Drain Voltage | V _{GD} | 20 | V |
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage (Reverse) | V _{GS} | 20 | V |
| Gate Current | I _G | 10 | mA |
| Power Dissipation | P _D | 360 | mW |
| Operating and Storage Junction Temperature | T _J , T _{STG} | -65 TO +150 | °C |

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNIT |
|----------------------|--|-----|------|------|
| I _{GSS} | V _{GS} =10V | | 20 | nA |
| I _{GSS} | V _{GS} =10V, T _A =100°C | | 2.0 | μA |
| I _{DSS} | V _{DS} =10V | 0.3 | 15 | mA |
| BV _{GSS} | I _G =10μA | 20 | | V |
| V _{GS} | V _{DS} =10V, I _D =30μA | 0.3 | 7.9 | V |
| V _{GS(OFF)} | V _{DS} =10V, I _D =10μA | | 8.0 | V |
| C _{iss} | V _{DS} =10V, V _{GS} =0, f=1.0MHz | | 32 | pF |
| C _{rss} | V _{DS} =10V, V _{GS} =0, f=1.0MHz | | 16 | pF |
| y _{fs1} | V _{DS} =10V, V _{GS} =0, f=1.0kHz | 800 | 5000 | μmho |
| y _{fs1} | V _{DS} =10V, V _{GS} =0, f=10MHz | 700 | | μmho |
| y _{os1} | V _{DS} =10V, V _{GS} =0, f=1.0kHz | | 200 | μmho |

OUTLINE DRAWING:



LEAD CODE:

1. DRAIN
2. GATE
3. SOURCE

145 Adams Avenue, Hauppauge, NY 11788 USA
 Tel: (631) 435-1110 • Fax: (631) 435-1824

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